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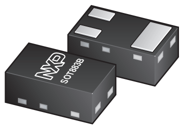


PMZB670UPE

20 V, single P-channel Trench MOSFET

Rev. 3 — 23 March 2012 **Product data sheet**

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ESD protection up to 2 kV
- Ultra thin package profile of 0.37 mm

1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

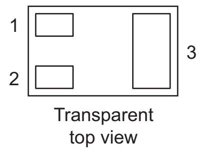
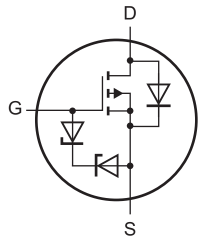
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I_D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-	-680	mA
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -400 mA; T_j = 25 °C		-	0.67	0.85	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 **DFN1006B-3 (SOT883B)**	 017aaa259
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZB670UPE	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

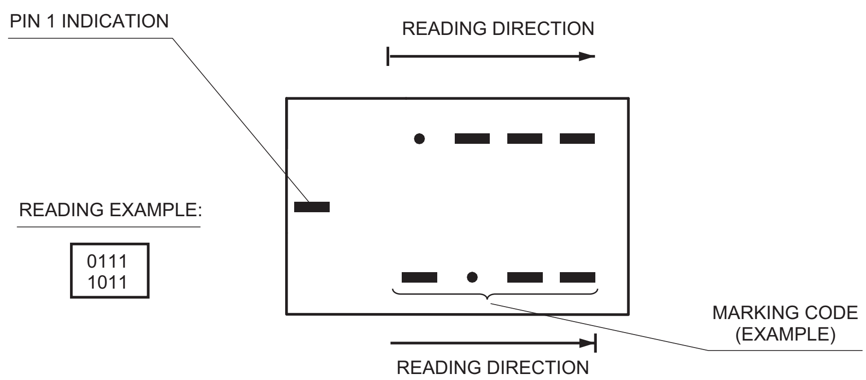
4. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMZB670UPE	0000 1011

[1] For DFN1006B-3 (SOT883B) binary marking code description see Figure 1.

4.1 Binary marking code description



006aac673

Fig 1. DFN1006B-3 (SOT883B) binary marking code description

5. Limiting values

Table 5. Limiting values

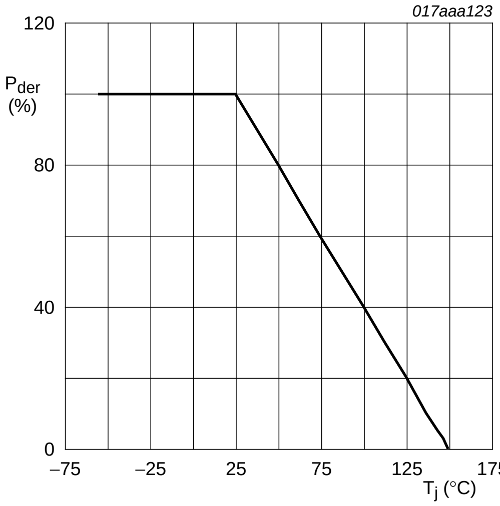
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-680	mA
		V_{GS} = -4.5 V; T_{amb} = 100 °C	[1]	-	-425	mA
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; t_p ≤ 10 µs		-	-2.7	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T_{sp} = 25 °C		-	2700	mW
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{amb} = 25 °C	[1]	-	-680	mA
ESD maximum rating						
V_{ESD}	electrostatic discharge voltage	HBM	[3]	-	2000	V

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2.

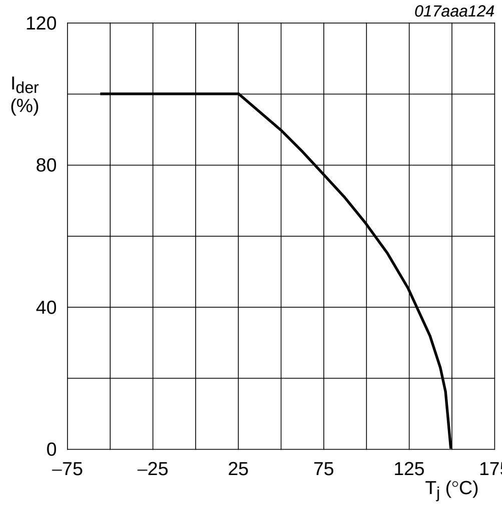
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



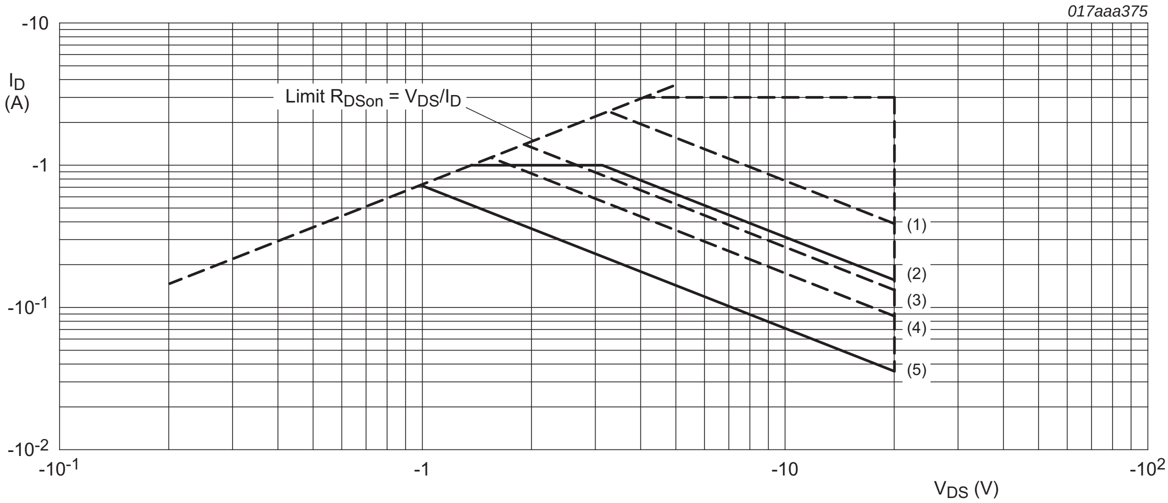
$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

Fig 2. Normalized total power dissipation as a function of junction temperature



$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$

Fig 3. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

(1) t_p = 1 ms

(2) DC; T_{sp} = 25 °C

(3) t_p = 10 ms

(4) t_p = 100 ms

(5) DC; T_{amb} = 25 °C; drain mounting pad 1 cm^2

Fig 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

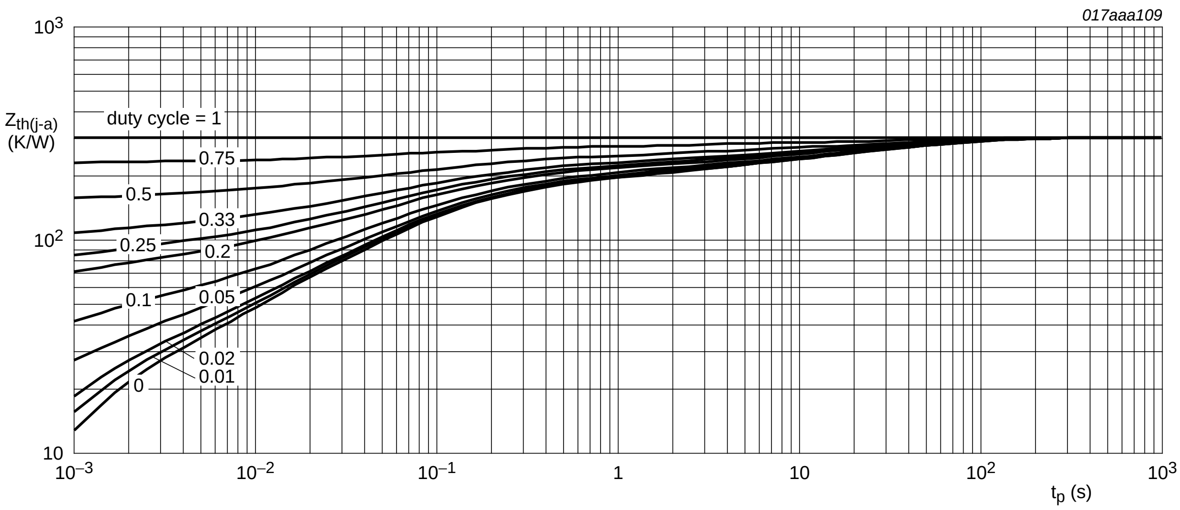
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	305	360	K/W
			[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	40	K/W

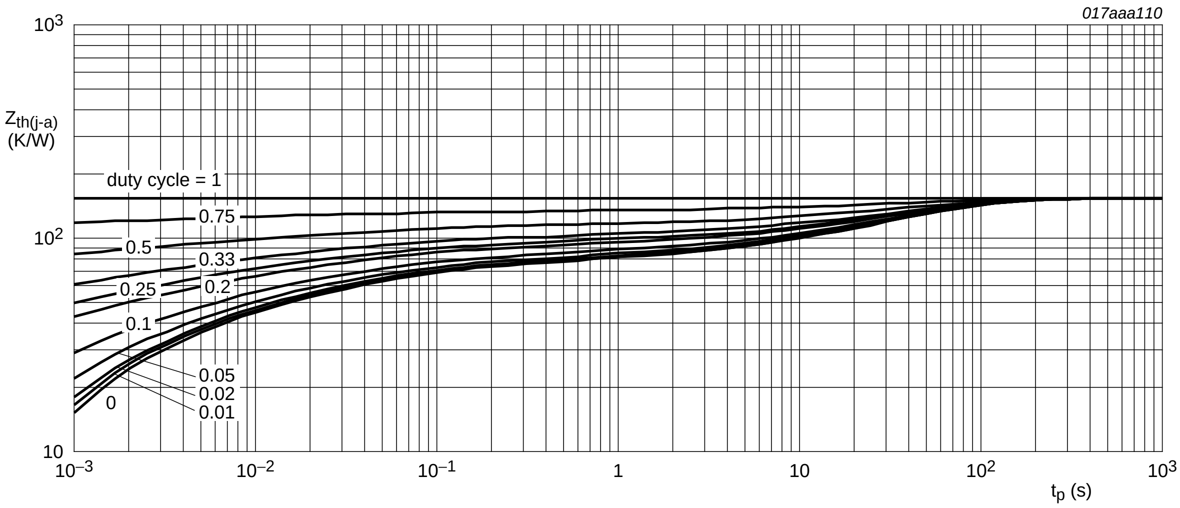
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2.



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



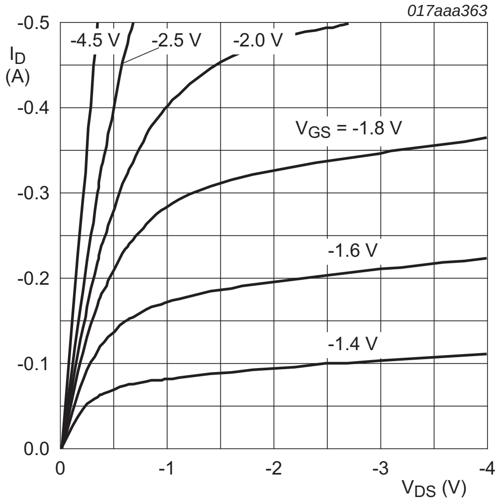
FR4 PCB, mounting pad for drain 1 cm^2

Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

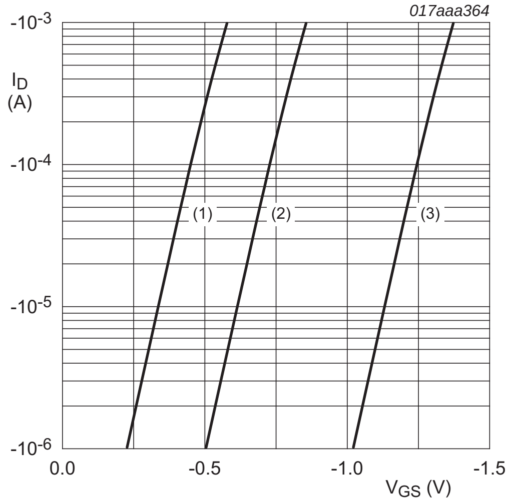
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS}; T_j = 25 °C	-0.5	-0.9	-1.3	V
I_{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	µA
		V_{DS} = -20 V; V_{GS} = 0 V; T_j = 150 °C	-	-	-10	µA
I_{GSS}	gate leakage current	V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-2	µA
		V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-2	µA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-0.5	µA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-0.5	µA
R_{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -400 mA; T_j = 25 °C	-	0.67	0.85	Ω
		V_{GS} = -4.5 V; I_D = -400 mA; T_j = 150 °C	-	1.1	1.4	Ω
		V_{GS} = -2.5 V; I_D = -200 mA; T_j = 25 °C	-	1.2	1.5	Ω
		V_{GS} = -1.8 V; I_D = -10 mA; T_j = 25 °C	-	1.8	2.8	Ω
g_{fs}	forward transconductance	V_{DS} = -10 V; I_D = -200 mA; T_j = 25 °C	-	610	-	mS
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	V_{DS} = -10 V; I_D = -400 mA; V_{GS} = -4.5 V; T_j = 25 °C	-	0.76	1.14	nC
Q_{GS}	gate-source charge		-	0.28	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C_{iss}	input capacitance	V_{DS} = -10 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C	-	58	87	pF
C_{oss}	output capacitance		-	21	-	pF
C_{rss}	reverse transfer capacitance		-	12	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = -10 V; R_L = 250 Ω; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C	-	18	36	ns
t_r	rise time		-	30	-	ns
$t_{d(off)}$	turn-off delay time		-	80	160	ns
t_f	fall time		-	72	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = -300 mA; V_{GS} = 0 V; T_j = 25 °C	-0.48	-0.84	-1.2	V



T_j = 25 °C

Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values



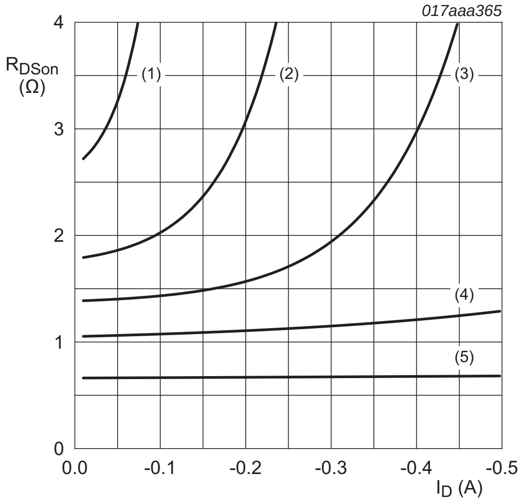
T_j = 25 °C; V_{DS} = -5 V

(1) minimum values

(2) typical values

(3) maximum values

Fig 8. Sub-threshold drain current as a function of gate-source voltage



T_j = 25 °C

(1) V_{GS} = -1.5 V

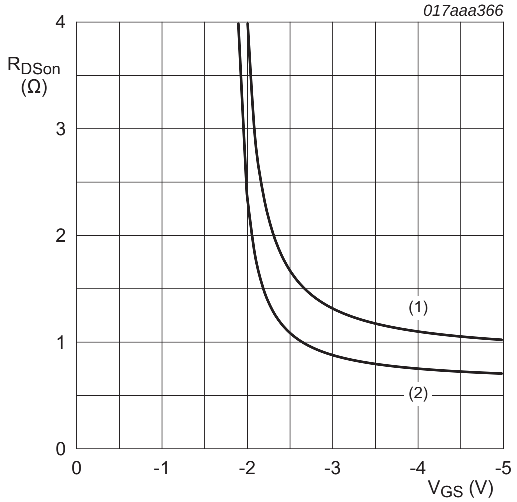
(2) V_{GS} = -1.8 V

(3) V_{GS} = -2.0 V

(4) V_{GS} = -2.5 V

(5) V_{GS} = -4.5 V

Fig 9. Drain-source on-state resistance as a function of drain current; typical values

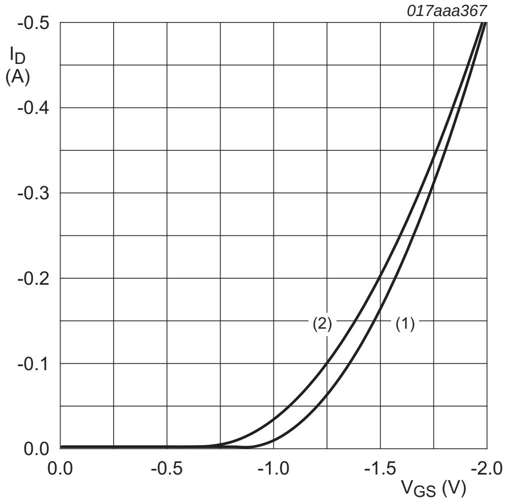


I_D = -400 mA

(1) T_j = 150 °C

(2) T_j = 25 °C

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

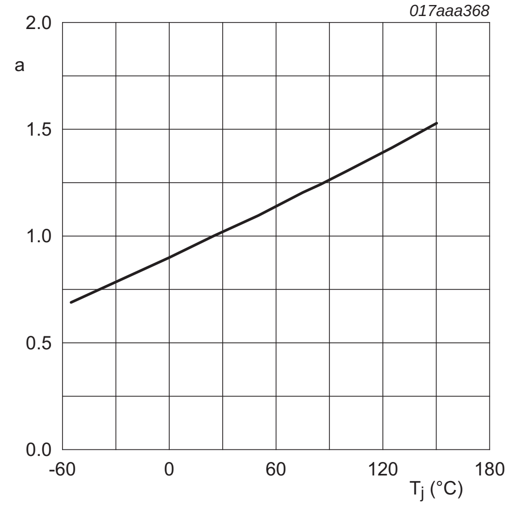


$V_{DS} > I_D \times R_{DSon}$

(1) T_j = 25 °C

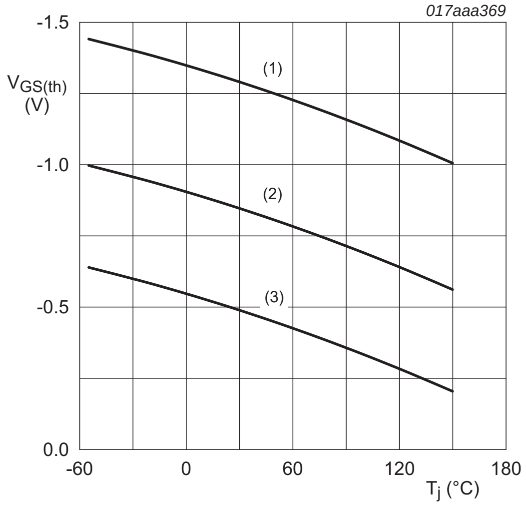
(2) T_j = 150 °C

Fig 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 12. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



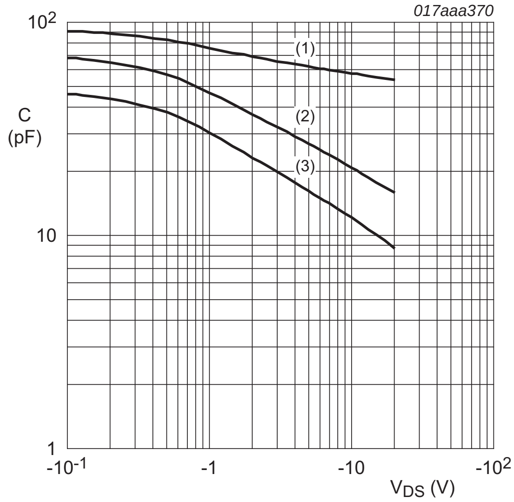
I_D = -0.25 mA; $V_{DS} = V_{GS}$

(1) maximum values

(2) typical values

(3) minimum values

Fig 13. Gate-source threshold voltage as a function of junction temperature



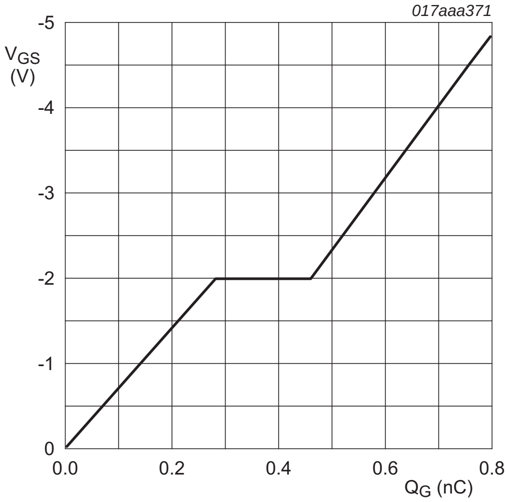
f = 1 MHz; V_{GS} = 0 V

(1) C_{iss}

(2) C_{oss}

(3) C_{rss}

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



I_D = -0.4 A; V_{DD} = -10 V; T_{amb} = 25 °C

Fig 15. Gate-source voltage as a function of gate charge; typical values

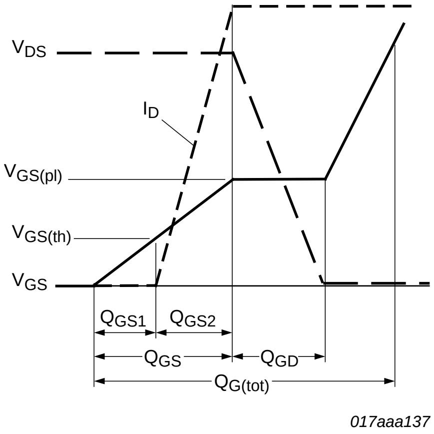
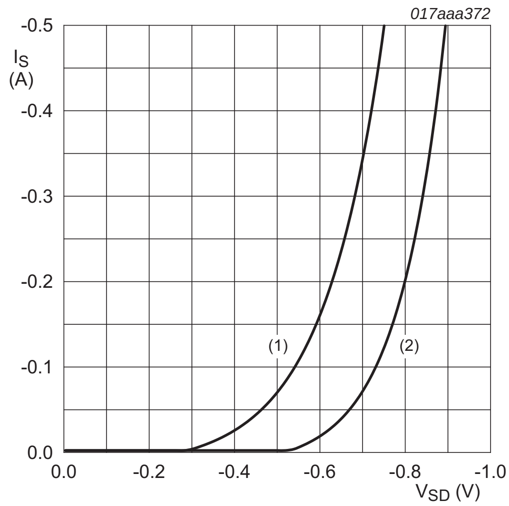


Fig 16. Gate charge waveform definitions



V_{GS} = 0 V

(1) T_{amb} = 150 °C

(2) T_{amb} = 25 °C

Fig 17. Source current as a function of source-drain voltage; typical values

8. Test information

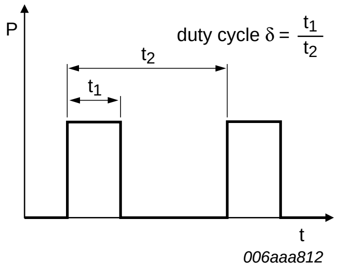


Fig 18. Duty cycle definition

9. Package outline

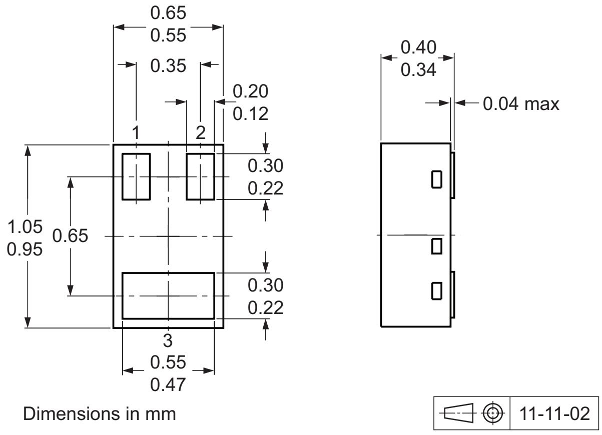


Fig 19. Package outline DFN1006B-3 (SOT883B)

10. Soldering

Footprint information for reflow soldering **SOT883B**

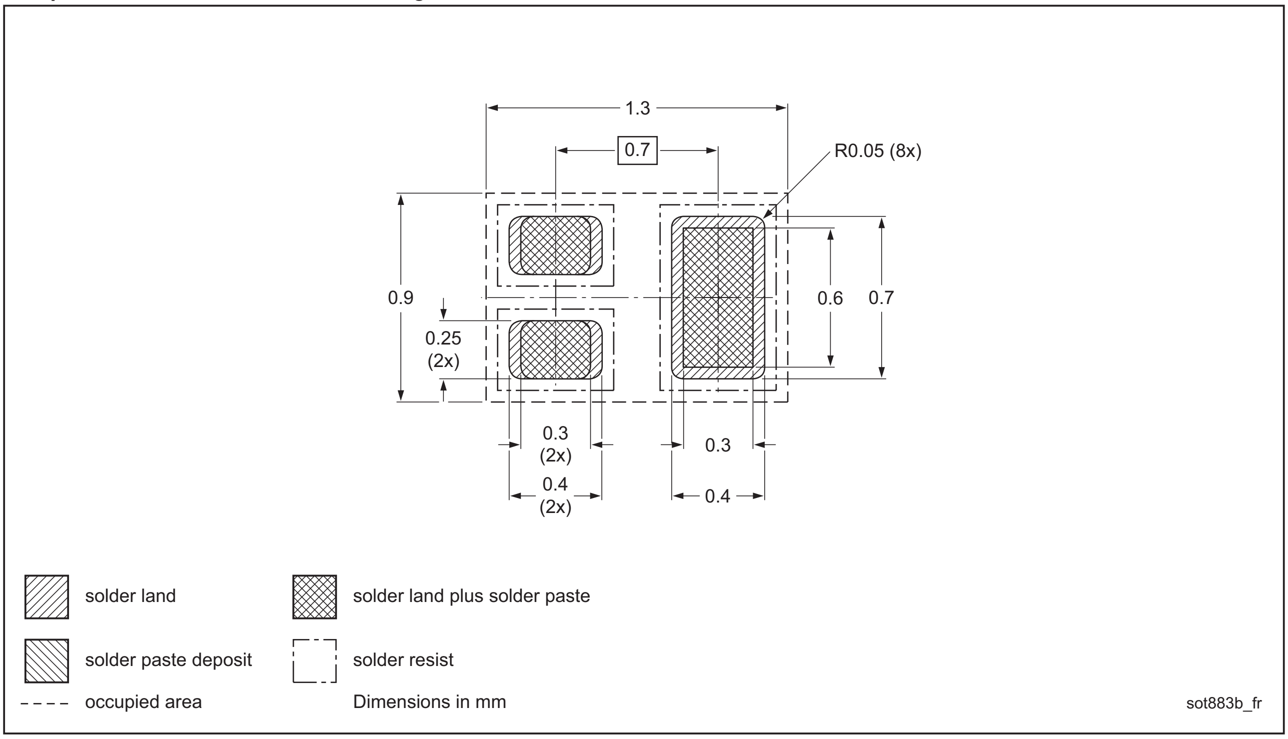


Fig 20. Reflow soldering footprint for DFN1006B-3 (SOT883B)

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMZB670UPE v.3	20120323	Product data sheet	-	PMZB670UPE v.2
Modifications:	• 1.2 “Features and benefits” is corrected.			
PMZB670UPE v.2	20120207	Product data sheet	-	PMZB670UPE v.1
PMZB670UPE v.1	20120131	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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14. Contents

For more information, please visit: http://www.nxp.com
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